anodizing the semi-conductor substrate at a third current density higher than said second current density to provide a third porous layer in or adjacent the second porous layer, the third porous layer having a third porosity higher than said second porosity;

forming at least one semi-conductor film on the surface and first porous layer; and

separating the semi-conductor film from the semi-conductor substrate along a line of relative weakness defined in the third porous layer or at or adjacent an interface defined between said third porous layer and the second porous layer,

wherein in said anodizing steps, the semi-conductor substrate is contacted by an electrolytic solution and exposed to a flow of current at said first, second and third current density, respectively, and wherein in the anodizing steps, the electrolytic solution is the same.

18 ~~21~~. A method for making a thin film semi-conductor comprising the steps of:

providing a semi-conductor substrate having a surface;

anodizing the semi-conductor substrate at a first current density to provide a first porous layer adjacent the surface having a first porosity;

anodizing the semi-conductor substrate at a second current density higher than said first current density to provide a second porous layer adjacent the first porous layer opposite the surface, the second porous layer having a second porosity greater than the

first porosity;

anodizing the semi-conductor substrate at a third current density higher than said second current density to provide a third porous layer in or adjacent the second porous layer, the third porous layer having a third porosity higher than said second porosity;

forming at least one semi-conductor film on the surface and first porous layer; and

separating the semi-conductor film from the semi-conductor substrate along a line of relative weakness defined in the third porous layer or at or adjacent an interface defined between said third porous layer and the second porous layer,

wherein in said anodizing steps, the semi-conductor substrate is contacted by an electrolytic solution and exposed to a flow of current at said first, second and third current density, respectively, and wherein the electrolytic solution used in the anodizing steps varies.

B cont'd

REMARKS

Applicant respectfully submits that this amendment is in full compliance with Rule 116 because it raises no new issues and either places all claims in a condition for allowance or in a better condition for appeal.

In the final Office Action, the prior rejections set forth under 35 U.S.C. § 112, second paragraph are withdrawn.

Claims 1-4 and 7-16 are rejected under 35 U.S.C. § 103 as being unpatentable over commonly assigned U.S. Patent No. 5,811,348 ("Matsushita"). In response, Applicant presents the remarks that

71